

CLAIM AMENDMENTS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1 (currently amended). A quasi-vertical semiconductor component, comprising:

a surface;

a semiconductor substrate;

a well;

at least two inner cells disposed in said well and ~~having a substantially similar operating point, thereby compensating for differences between said inner cells;~~

a buried layer disposed between said well and said semiconductor substrate; and

a sinker zone disposed outside a region of said inner cells and defining a sinker voltage, said sinker zone connecting

said buried layer to said surface of the semiconductor component; and

said inner cells having substantially similar values for forward currents and reverse currents being independent of a positional relationship to said sinker zone by varying a given width of said inner cells and/or a given radius of curvature of said inner cells and/or a spacing between said inner cells in dependence on the sinker voltage.

2 (canceled).

3 (currently amended). The semiconductor component according to claim 1 2, wherein said inner cells have body zones with a given width and a given radius of curvature, and that at least one of said given width of said body zones, said given radius of curvature of said body zones, and a spacing between grid configuration of said body zones of said inner cells is varied.

4 (currently amended). The semiconductor component according to claim 3, wherein said body zones are one of wider and and/or have a larger radius of curvature in a vicinity of said sinker zone than at a distance from said sinker zone.

5 (currently amended). The semiconductor component according to claim 3, wherein said spacing between grid configuration of said inner cells has a larger spacing distance at a distance from said sinker zone than in a vicinity of said sinker zone.

6 (currently amended). The semiconductor component according to claim 1 2, further comprising doped regions disposed in said well, a variation of at least one of said given width, said given radius of curvature and said spacing between grid configuration of said inner cells zones is effected by said doped regions.

7 (original). The semiconductor component according to claim 6, wherein said doped regions are introduced by high-energy ion implantation.

8 (original). The semiconductor component according to claim 7, wherein said doped regions lie between said well and said body zone of said inner cells.

9 (original). The semiconductor component according to claim 1, wherein said well has an edge region and said sinker zone is disposed at said edge region.